

# **ISC Silicon NPN RF Transistor**

2SC3357

#### **DESCRIPTION**

· Low Noise and High Gain

NF = 1.1 dB TYP.,  $G_a = 8.0 \text{ dB TYP.}$ 

 $@V_{CE} = 10 \text{ V}, I_C = 7 \text{ mA}, f = 1.0 \text{ GHz}$ 

NF = 1.8 dB TYP.,  $G_a = 9.0 \text{ dB TYP.}$ 

 $@V_{CE} = 10 \text{ V}, I_{C} = 40 \text{ mA}, f = 1.0 \text{ GHz}$ 

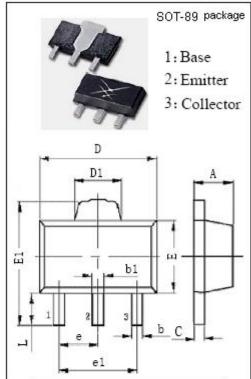
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



 Designed for low noise amplifier at VHF, UHF and CATV band.

# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	20	V
V <sub>CEO</sub>	Collector-Emitter Voltage	12	V
V <sub>EBO</sub>	Emitter-Base Voltage	3.0	V
Ic	Collector Current-Continuous	0.1	Α
Pc	Collector Power Dissipation @T <sub>C</sub> =25°C	1.2	W
TJ	Junction Temperature	150	$^{\circ}$ C
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C



	mm		
DIM	MIN	MAX	
A	1.40	1.60	
b	0.32	0.52	
b1	0. 36	0. 56	
С	0.35	0.44	
D	4.40	4.46	
D1	1.40	1.80	
E	2.30	2.60	
E1	3. 94	4. 25	
е	1.50typ		
e1	2. 90	3. 10	
L	0.90	1. 10	



# **ISC Silicon NPN RF Transistor**

2SC3357

### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 10V; I <sub>E</sub> = 0			1.0	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 1V; I <sub>C</sub> = 0			1.0	μА
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 20mA ; V <sub>CE</sub> = 10V	50		300	
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 20mA ; V <sub>CE</sub> = 10V		6.5		GHz
C <sub>re</sub>	Feed-Back Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V;f= 1.0MHz		0.65	1.0	pF
S <sub>21e</sub>   <sup>2</sup>	Insertion Power Gain	I <sub>C</sub> = 20mA ; V <sub>CE</sub> = 10V;f= 1.0GHz		9		dB
NF	Noise Figure	I <sub>C</sub> = 7mA ; V <sub>CE</sub> = 10V;f= 1.0GHz		1.1		dB
NF	Noise Figure	I <sub>C</sub> = 40mA ; V <sub>CE</sub> = 10V;f= 1.0GHz		1.8	3.0	dB

## ♦ h<sub>FE</sub> Classification

Marking	RH	RF	RE
h <sub>FE</sub>	50-100	80-160	125-250

### **NOTICE:**

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

isc website: www.iscsemi.cn